

## Power MOSFET

**D<sup>2</sup>PAK (TO-263)**


N-Channel MOSFET



**RoHS\***  
Available  
**HALOGEN**  
**FREE**  
Available

### FEATURES

- Dynamic dV/dt rating
- Repetitive avalanche rated
- Fast switching
- Ease of paralleling
- Simple drive requirements
- Material categorization: for definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)

### Note

\* This datasheet provides information about parts that are RoHS-compliant and / or parts that are non RoHS-compliant. For example, parts with lead (Pb) terminations are not RoHS-compliant. Please see the information / tables in this datasheet for details

### DESCRIPTION

Third generation MOSFETs from Vishay provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The D<sup>2</sup>PAK (TO-263) package is universally preferred for all commercial-industrial applications at power dissipation levels to approximately 50 W. The low thermal resistance and low package cost of the D<sup>2</sup>PAK (TO-263) contribute to its wide acceptance throughout the industry.

### PRODUCT SUMMARY

V <sub>DS</sub> (V)	900	
R <sub>DS(on)</sub> (Ω)	V <sub>GS</sub> = 10 V	3.7
Q <sub>g</sub> max. (nC)	78	
Q <sub>gs</sub> (nC)	10	
Q <sub>gd</sub> (nC)	42	
Configuration	Single	

### ORDERING INFORMATION

Package	D <sup>2</sup> PAK (TO-263)	D <sup>2</sup> PAK (TO-263)
Lead (Pb)-free and Halogen-free	SiHFBF30S-GE3	-
Lead (Pb)-free	IRFBF30STRLPbF	IRFBF30STRRPbF

### ABSOLUTE MAXIMUM RATINGS (T<sub>C</sub> = 25 °C, unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNIT	
Drain-source voltage	V <sub>DS</sub>	900	V	
Gate-source voltage	V <sub>GS</sub>	± 20		
Continuous drain current	V <sub>GS</sub> at 10 V	T <sub>C</sub> = 25 °C	A	
		T <sub>C</sub> = 100 °C		2.3
Pulsed drain current <sup>a</sup>	I <sub>DM</sub>	14		
Linear derating factor		1.0	W/°C	
Single pulse avalanche energy <sup>b</sup>	E <sub>AS</sub>	250	mJ	
Repetitive avalanche current <sup>a</sup>	I <sub>AR</sub>	3.6	A	
Repetitive avalanche energy <sup>a</sup>	E <sub>AR</sub>	13	mJ	
Maximum power dissipation	T <sub>C</sub> = 25 °C	P <sub>D</sub>	125	W
Peak diode recovery dV/dt <sup>c</sup>	dV/dt	1.5	V/ns	
Operating junction and storage temperature range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C	
Soldering recommendations (peak temperature) <sup>d</sup>	For 10 s	300		

### Notes

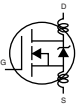

- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11)
- V<sub>DD</sub> = 50 V, starting T<sub>J</sub> = 25 °C, L = 36 mH, R<sub>g</sub> = 25 Ω, I<sub>AS</sub> = 3.6 A (see fig. 12)
- I<sub>SD</sub> ≤ 3.6 A, dI/dt ≤ 70 A/μs, V<sub>DD</sub> ≤ 600, T<sub>J</sub> ≤ 150 °C
- 1.6 mm from case



THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum junction-to-ambient	$R_{thJA}$	-	62	°C/W
Maximum junction-to-ambient (PCB mount) <sup>a</sup>	$R_{thJA}$	-	40	
Maximum junction-to-case (drain)	$R_{thJC}$	-	1.0	

**Note**

a. When mounted on 1" square PCB (FR-4 or G-10 material)

SPECIFICATIONS ( $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
<b>Static</b>						
Drain-source breakdown voltage	$V_{DS}$	$V_{GS} = 0, I_D = 250\text{ }\mu\text{A}$	900	-	-	V
$V_{DS}$ temperature coefficient	$\Delta V_{DS}/T_J$	Reference to $25\text{ }^\circ\text{C}$ , $I_D = 1\text{ mA}$	-	1.1	-	V/°C
Gate-source threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	2.0	-	4.0	V
Gate-source leakage	$I_{GSS}$	$V_{GS} = \pm 20\text{ V}$	-	-	$\pm 100$	nA
Zero gate voltage drain current	$I_{DSS}$	$V_{DS} = 900\text{ V}, V_{GS} = 0\text{ V}$	-	-	100	$\mu\text{A}$
		$V_{DS} = 720\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$	-	-	500	
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 2.2\text{ A}^b$	-	-	3.7	$\Omega$
Forward transconductance	$g_{fs}$	$V_{DS} = 100\text{ V}, I_D = 2.2\text{ A}^b$	2.3	-	-	S
<b>Dynamic</b>						
Input capacitance	$C_{iss}$	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1.0\text{ MHz}$ , see fig. 5	-	1200	-	$\mu\text{F}$
Output capacitance	$C_{oss}$		-	320	-	
Reverse transfer capacitance	$C_{rss}$		-	200	-	
Total gate charge	$Q_g$	$V_{GS} = 10\text{ V}, I_D = 3.6\text{ A}, V_{DS} = 360\text{ V}$ , see fig. 6 and 13 <sup>b</sup>	-	-	78	nC
Gate-source charge	$Q_{gs}$		-	-	10	
Gate-drain charge	$Q_{gd}$		-	-	42	
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 450\text{ V}, I_D = 3.6\text{ A}, R_g = 12\text{ }\Omega, R_D = 120\text{ }\Omega$ , see fig. 10 <sup>b</sup>	-	14	-	ns
Rise time	$t_r$		-	25	-	
Turn-off delay time	$t_{d(off)}$		-	90	-	
Fall time	$t_f$		-	30	-	
Gate input resistance	$R_g$	$f = 1\text{ MHz}$ , open drain	0.4	-	2.0	$\Omega$
Internal drain inductance	$L_D$	Between lead, 6 mm (0.25") from package and center of die contact 	-	4.5	-	nH
Internal source inductance	$L_S$		-	7.5	-	
<b>Drain-Source Body Diode Characteristics</b>						
Continuous source-drain diode current	$I_S$	MOSFET symbol showing the integral reverse p - n junction diode 	-	-	3.6	A
Pulsed diode forward current <sup>a</sup>	$I_{SM}$		-	-	14	
Body diode voltage	$V_{SD}$	$T_J = 25\text{ }^\circ\text{C}, I_S = 3.6\text{ A}, V_{GS} = 0\text{ V}^b$	-	-	1.8	V
Body diode reverse recovery time	$t_{rr}$	$T_J = 25\text{ }^\circ\text{C}, I_F = 3.6\text{ A}, dI/dt = 100\text{ A}/\mu\text{s}^b$	-	430	650	ns
Body diode reverse recovery charge	$Q_{rr}$		-	1.4	2.1	$\mu\text{C}$
Forward turn-on time	$t_{on}$	Intrinsic turn-on time is negligible (turn-on is dominated by $L_S$ and $L_D$ )				

**Notes**

- a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11)
- b. Pulse width  $\leq 300\text{ }\mu\text{s}$ ; duty cycle  $\leq 2\%$

**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)

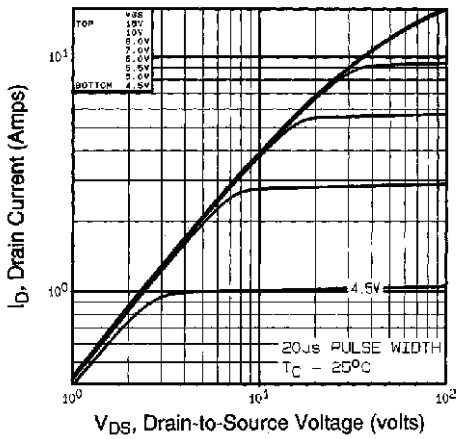


Fig. 1 - Typical Output Characteristics,  $T_C = 25\text{ }^\circ\text{C}$

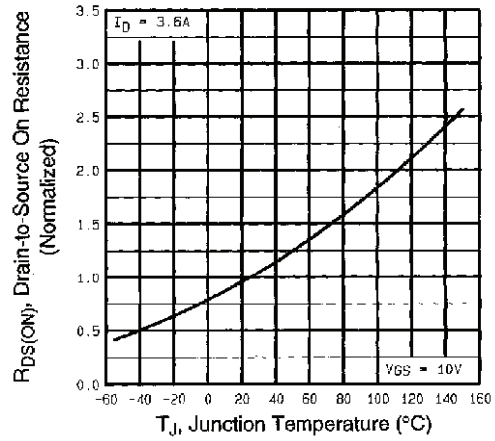


Fig. 4 - Normalized On-Resistance vs. Temperature

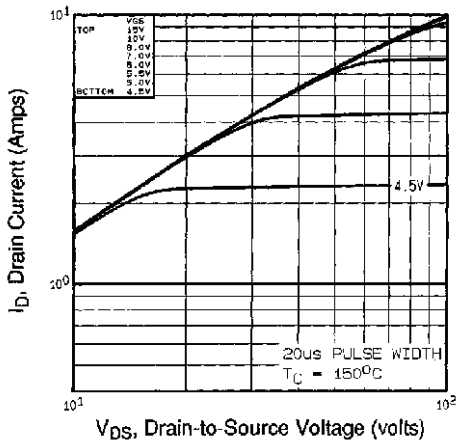


Fig. 2 - Typical Output Characteristics,  $T_C = 150\text{ }^\circ\text{C}$

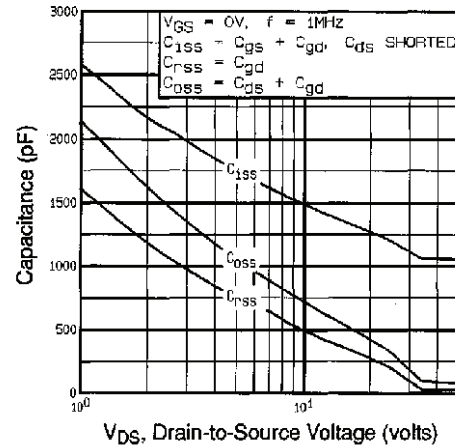


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

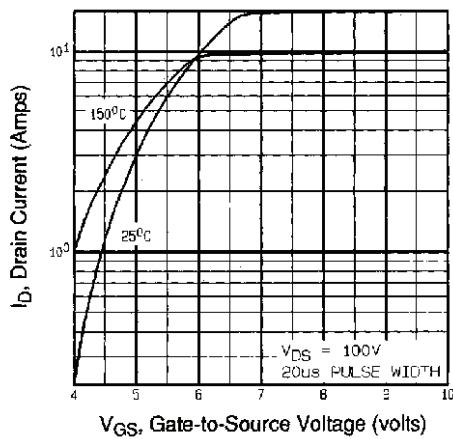


Fig. 3 - Typical Transfer Characteristics

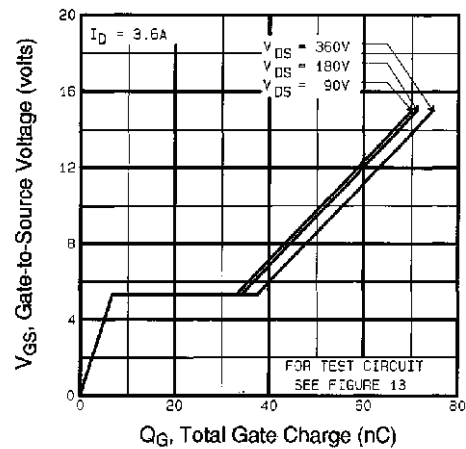


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)

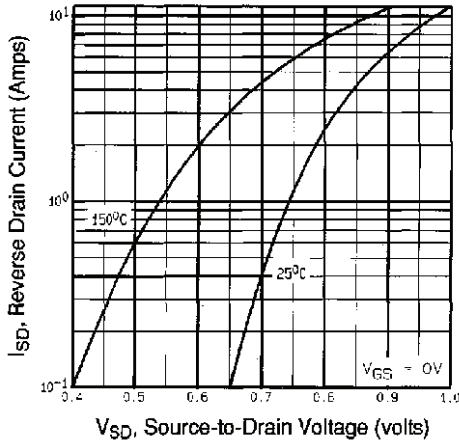


Fig. 7 - Typical Source-Drain Diode Forward Voltage

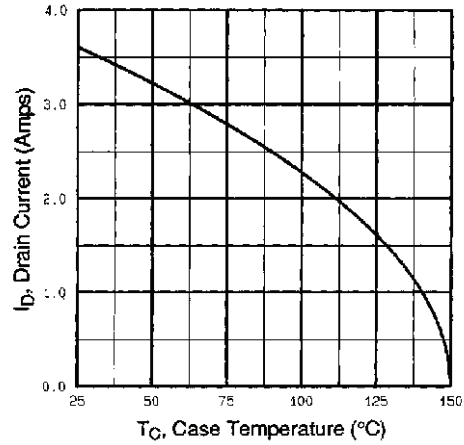


Fig. 9 - Maximum Drain Current vs. Case Temperature

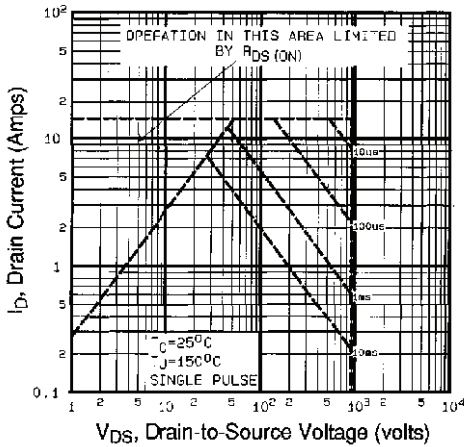


Fig. 8 - Maximum Safe Operating Area

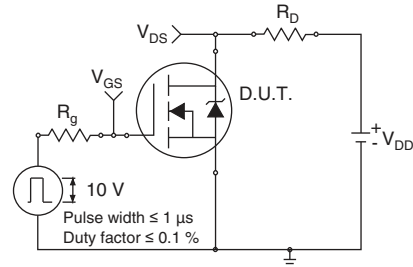


Fig. 10 - Switching Time Test Circuit

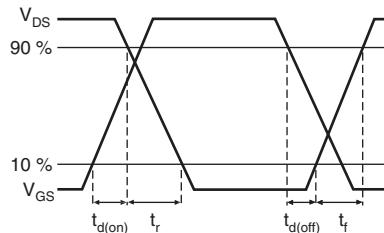


Fig. 11 - Switching Time Waveforms

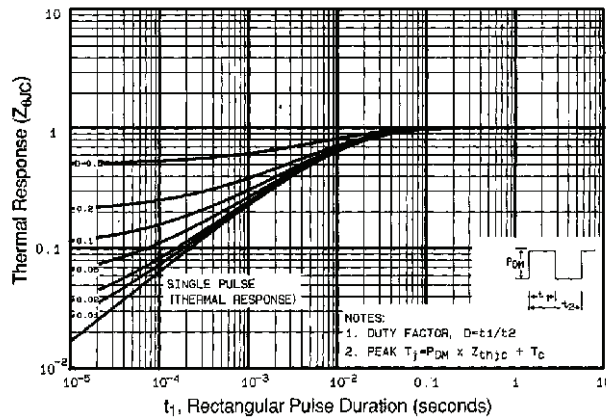
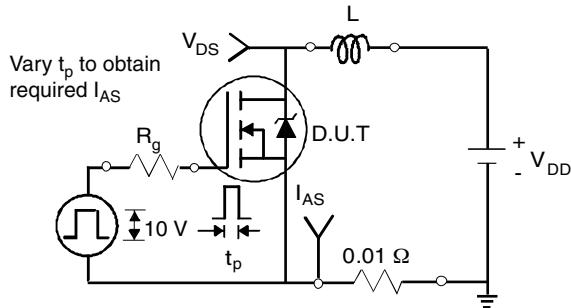
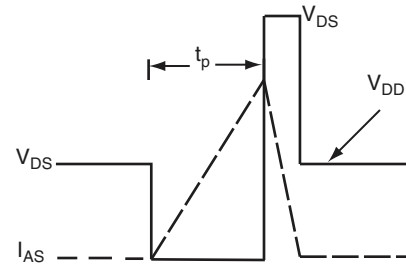


Fig. 12 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

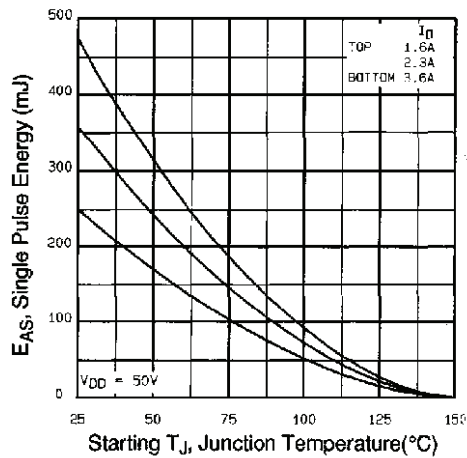
**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



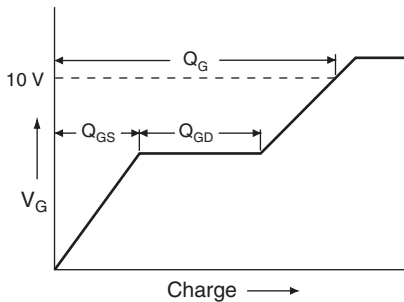
**Fig. 13 - Unclamped Inductive Test Circuit**



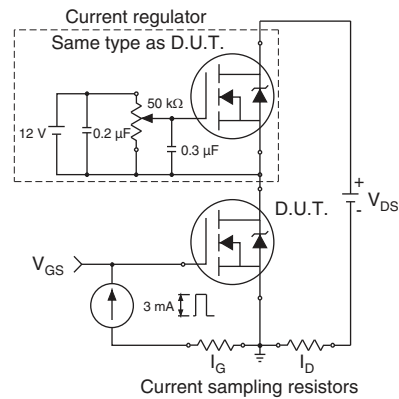
**Fig. 14 - Unclamped Inductive Waveforms**



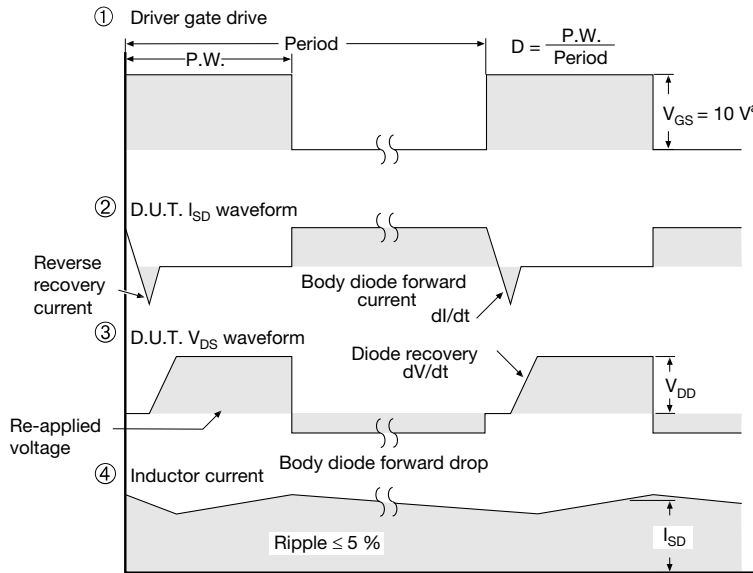
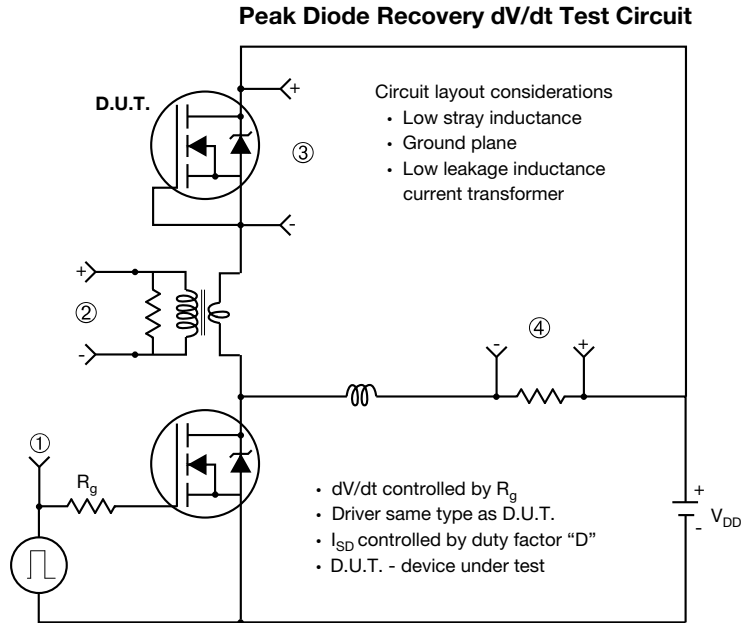
**Fig. 15 - Maximum Avalanche Energy vs. Drain Current**



**Fig. 16 - Basic Gate Charge Waveform**



**Fig. 17 - Gate Charge Test Circuit**



**Note**

a.  $V_{GS} = 5 V$  for logic level devices

**Fig. 18 - For N-Channel**

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see [www.vishay.com/ppg?91389](http://www.vishay.com/ppg?91389).

### TO-263AB (HIGH VOLTAGE)



DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	4.06	4.83	0.160	0.190
A1	0.00	0.25	0.000	0.010
b	0.51	0.99	0.020	0.039
b1	0.51	0.89	0.020	0.035
b2	1.14	1.78	0.045	0.070
b3	1.14	1.73	0.045	0.068
c	0.38	0.74	0.015	0.029
c1	0.38	0.58	0.015	0.023
c2	1.14	1.65	0.045	0.065
D	8.38	9.65	0.330	0.380

DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
D1	6.86	-	0.270	-
E	9.65	10.67	0.380	0.420
E1	6.22	-	0.245	-
e	2.54 BSC		0.100 BSC	
H	14.61	15.88	0.575	0.625
L	1.78	2.79	0.070	0.110
L1	-	1.65	-	0.066
L2	-	1.78	-	0.070
L3	0.25 BSC		0.010 BSC	
L4	4.78	5.28	0.188	0.208

ECN: S-82110-Rev. A, 15-Sep-08  
DWG: 5970

#### Notes

1. Dimensioning and tolerancing per ASME Y14.5M-1994.
2. Dimensions are shown in millimeters (inches).
3. Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body at datum A.
4. Thermal PAD contour optional within dimension E, L1, D1 and E1.
5. Dimension b1 and c1 apply to base metal only.
6. Datum A and B to be determined at datum plane H.
7. Outline conforms to JEDEC outline to TO-263AB.

**RECOMMENDED MINIMUM PADS FOR D<sup>2</sup>PAK: 3-Lead**



Recommended Minimum Pads  
Dimensions in Inches/(mm)

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